# Eric S Hellman

List of Publications by Year
in descending order

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|---|---|---|---|
| 50 papers | 1,667 citations | 257101 24 h-index | 276539 41 g-index |
| 50 all docs | 50 docs citations | 50 times ranked | 1015 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Electron affinity at aluminum nitride surfaces. Applied Physics Letters, 1998, 73, 1346-1348. | 1.5 | 93 |
| 2 | The Polarity of GaN: a Critical Review. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1. | 1.0 | 282 |
| 3 | High resolution transmission electron microscopy of Ba<sub>1â^'x</sub>K<sub>x</sub>BiO<sub>3</sub> superconductor-insulator-superconductor grain boundary tunnel junctions. Journal of Materials Research, 1998, 13, 1774-1779. | 1.2 | 5 |
| 4 | Nucleation of AlN on the (7Ã—7) Reconstructed Silicon (1 1 1) Surface. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1. | 1.0 | 17 |
| 5 | Epitaxial Growth and Orientation of GaN on (1 0 0) Î³-LiAlO2. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1. | 1.0 | 66 |
| 6 | Nonuniform Morphology and Luminescence Properties of a Molecular Beam Epitaxy GaN Film from Atomic Force Microscopy, Scanning Electron Microscopy and Cathodoluminescence. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1. | 1.0 | 5 |
| 7 | ScAlMgO<sub>4</sub>: an Oxide Substrate for GaN Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1. | 1.0 | 45 |
| 8 | Growth of Ga-face and N-face GaN films using ZnO Substrates. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1. | 1.0 | 67 |
| 9 | Origin of the Ï• â^¼ Â±9Â° peaks in YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7â^'Î´</sub> films grown on cubic zirconia substrates. Journal of Materials Research, 1996, 11, 1336-1348. | 1.2 | 21 |
| 10 | ScAlMgO<sub>4</sub>: An Oxide Substrate for GaN Epitaxy. Materials Research Society Symposia Proceedings, 1995, 395, 51. | 0.1 | 25 |
| 11 | Evidence for two-particle normal-state tunneling inBa1â^'xKxBiO3native-barrier tunnel junctions. Physical Review B, 1995, 52, 6822-6828. | 1.1 | 15 |
| 12 | Epitaxial solidâ€solution films of immiscible MgO and CaO. Applied Physics Letters, 1994, 64, 1341-1343. | 1.5 | 28 |
| 13 | Penetration depth, microwave surface resistance, and gap ratio in NbN and Ba1â^'xKxBiO3thin films. Applied Physics Letters, 1994, 64, 244-246. | 1.5 | 39 |
| 14 | Far-infrared transmission ofBa1â^'xKxBiO3thin films. Physical Review B, 1994, 50, 643-646. | 1.1 | 12 |
| 15 | Epitaxial Solid-Solution Films of Immiscible MgO and CaO. Materials Research Society Symposia Proceedings, 1994, 341, 127. | 0.1 | 1 |
| 16 | Angular dependence of tunneling effects in Ba 1-x K x BiO 3 grain boundaries. , 1994, 2158, 124. | | 1 |
| 17 | Normal-state resistivity and Hall effect inBa1â^'xKxBiO3epitaxial films. Physical Review B, 1993, 47, 11346-11353. | 1.1 | 53 |
| 18 | Hysteretic Josephson-junction behavior and phase diffusion inBa1â^'xKxBiO3films. Physical Review B, 1993, 48, 6626-6631. | 1.1 | 6 |

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|---|---|---|---|
| 19 | Quasiparticle-tunneling properties ofBa1â^'xKxBiO3/BaBi2Oy/Ba1â^'xKxBiO3sandwich junctions. Physical Review B, 1993, 47, 14510-14513. | 1.1 | 10 |
| 20 | Superconductorâ€insulatorâ€superconductor tunneling in Ba1â^'xKxBiO3grain boundaries. Applied Physics Letters, 1993, 63, 2824-2826. | 1.5 | 37 |
| 21 | Molecular beam epitaxy of dysprosium barium cuprous oxides using molecular oxygen. Journal of Materials Research, 1992, 7, 795-800. | 1.2 | 11 |
| 22 | Free-charge-carrier plasmons inBa1â^'xKxBiO3: A close relation to cuprate superconductors. Physical Review B, 1992, 46, 1182-1187. | 1.1 | 29 |
| 23 | Tc-Î´ Relations in YB2Cu3O7-Î´ Thin Films: Effects of Oxygen Pressure During Growth. Materials Research Society Symposia Proceedings, 1992, 275, 101. | 0.1 | 1 |
| 24 | Molecular Beam Epitaxy of Ba1-xKxBiO3 Films and Heterostructures. , 1992, , 855-858. | | 0 |
| 25 | Epitaxial Ba1â^'xKxBiO3films on MgO: Nucleation, cracking, and critical currents. Applied Physics Letters, 1991, 58, 1335-1337. | 1.5 | 67 |
| 26 | Public Sees Physicists in the Wrong Light. Physics Today, 1991, 44, 100-100. | 0.3 | 0 |
| 27 | Molecular Beam Epitaxy of Superconducting Bismuthates on Various Substrates. Materials Research Society Symposia Proceedings, 1991, 221, 53. | 0.1 | 2 |
| 28 | Variable-range-hopping transport inBa1â^'xKxBiO3(0<x<0.35). Physical Review B, 1991, 44, 9719-9722. | 1.1 | 24 |
| 29 | The effects of oxidation and air exposure on RbxBa1â^'xBiO3 superconducting thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 2716-2720. | 0.9 | 12 |
| 30 | Allâ€highTcJosephson tunnel junction: Ba1â^'xKxBiO3/Ba1â^'xKxBiO3junctions. Applied Physics Letters, 1991, 58, 95-96. | 1.5 | 63 |
| 31 | Electron tunneling in the high-Tcbismuthate superconductors. Physical Review B, 1991, 44, 12521-12524. | 1.1 | 67 |
| 32 | Circular dichroism observed in bismuthate superconductors. Physical Review B, 1991, 43, 11408-11410. | 1.1 | 12 |
| 33 | (Rubidium,Barium) Bismuth Oxide: A Model Material For Molecular Beam Epitaxy Of Perovskites. Proceedings of SPIE, 1990, , . | 0.8 | 1 |
| 34 | Adsorption controlled molecular beam epitaxy of rubidium barium bismuth oxide. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 332. | 1.6 | 29 |
| 35 | Optical characterization of excited states inBaBiO3. Physical Review B, 1990, 42, 923-926. | 1.1 | 25 |
| 36 | Molecular beam epitaxy of superconducting (Rb,Ba)BiO3. Applied Physics Letters, 1989, 55, 2120-2122. | 1.5 | 46 |

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|---|---|---|---|
| 37 | Umklapp electron-electron scattering resistivity of half-filled copper-oxygen chains and planes. Physical Review B, 1989, 39, 9604-9606. | 1.1 | 3 |
| 38 | Molecular Beam Epitaxy of Rubidium Barium Bismuth Oxide: Structural Phenomena in Perovskite Heteroepitaxy. Materials Research Society Symposia Proceedings, 1989, 169, 719. | 0.1 | 1 |
| 39 | Phase characterization of dysprosium barium copper oxide thin films grown on strontium titanate by molecular beam epitaxy. Journal of Materials Research, 1989, 4, 476-495. | 1.2 | 20 |
| 40 | Elastic scattering centers in resonant tunneling diodes. Applied Physics Letters, 1988, 53, 201-203. | 1.5 | 55 |
| 41 | Limit cycle oscillation in negative differential resistance devices. Journal of Applied Physics, 1988, 64, 2798-2800. | 1.1 | 13 |
| 42 | Molecular-beam epitaxy and deposition of high-Tc superconductors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 799. | 1.6 | 28 |
| 43 | Molecular beam epitaxy of layered Dyâ€Baâ€Cuâ€O compounds. Applied Physics Letters, 1988, 53, 1660-1662. | 1.5 | 66 |
| 44 | The Effect Of Elastic Scattering Centers On The Current Voltage Characteristics Of Double Barrier Resonant Tunneling Diodes. Proceedings of SPIE, 1988, , . | 0.8 | 0 |
| 45 | Growth of highTcsuperconducting thin films using molecular beam epitaxy techniques. Applied Physics Letters, 1987, 51, 1191-1193. | 1.5 | 128 |
| 46 | Infra-red transmission spectroscopy of GaAs during molecular beam epitaxy. Journal of Crystal Growth, 1987, 81, 38-42. | 0.7 | 64 |
| 47 | Reduction of the acceptor impurity background in GaAs grown by molecular beam epitaxy. Applied Physics Letters, 1986, 49, 391-393. | 1.5 | 27 |
| 48 | Molecular beam epitaxy of gallium arsenide using direct radiative substrate heating. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 574. | 1.6 | 22 |
| 49 | Mechanism of current modulation by optic phonons in heterojunction tunneling experiments. Physical Review B, 1986, 34, 5475-5483. | 1.1 | 6 |
| 50 | Energy-momentum relation for polarons confined to one dimension. Physical Review B, 1986, 33, 8284-8290. | 1.1 | 17 |